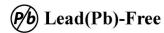
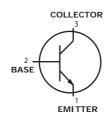
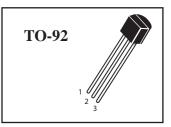
BC556, A/B BC557, A/B/C BC558, A/B/C

# **PNP** General Purpose Transistor







### **Maximum Ratings** (TA=25°C unless otherwise noted)

Rating	Symbol	BC556	BC557	BC558	Unit
Collector-Emitter Voltage	VECO	-65	-45	-30	Vdc
Collector-Base Voltage	VCBO	-80	-50	-30	Vdc
Emitter-Base Voltage	VEBO	-5	-5	-5	Vdc
Collector Current Continuous	IC		100		mAdc

#### THERMAL CHARACTERISTICS

Characteristics		Symbol	Max	Unit	
Total Device Dissipation Alumina Substrate, T <sub>A</sub> = 25°C	BC556 BC557 BC558	P <sub>D</sub>	625	mW/ °C	
Junction and Storage, Temperature	BC556 BC557 BC558	T <sub>J, Tstg</sub>	-55 to +150	°C	

### **ELECTRICAL CHARACTERISTICS**

Characteristics	Symbol	Min	Max	Unit	]
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#### **OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage $(I_C = 2 \text{ mAdc. } I_B = 0)$	BC556 BC557 BC558	V <sub>(BR)CEO</sub>	-65 -45 -30	- - -	Vdc
Collector-Base Breakdown Voltage ( $I_C = 100 \mu Adc. I_E = 0$ )	BC556 BC557 BC558	V <sub>(BR)CBO</sub>	-80 -50 -30	- - -	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 100 \mu Adc. I_C = 0$ )	BC556 BC557 BC558	V <sub>(BR)EBO</sub>	-5	-	Vdc



 $\textbf{ELECTRICAL CHARACTERISTICS} \text{ (T}_{A} = 25^{\circ}\text{C unless otherwise noted) (Countinued)}$ 

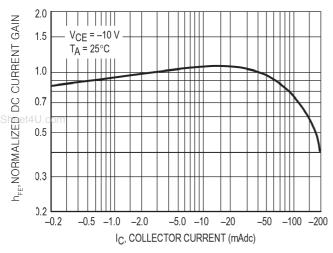
Characteristics		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector Cutoff Current (VCE=-60V, IB=0) (VCE=-40V, IB=0) (VCE=25V, IB=0)	BC556 BC557 BC558	ICEO	- - -	-0.1	μА
Collector Cutoff Current  (VCB=-70V, IE=0)  (VCB=-45V, IE=0)  (VCB=-25V, IE=0)	BC556 BC557 BC558	ICBO	- - -	-0.1	μА
Emitter Cutoff Current (V <sub>EB</sub> =-5.0 Vdc, I <sub>C</sub> =0)	BC556 BC557 BC558	I <sub>EBO</sub>	-	-0.1	μА

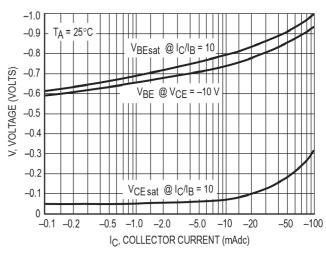
#### **ON CHARACTERISTICS**

THE CHARACTERISTICS					
DC current gain	BC556		120	500	
(VCE=-5V, Ic=-2mA)	BC557		120	800	
	BC558	h <sub>FE</sub>	120	800	
	BC556A/BC557A/BC558A	FE	120	220	
	BC556B/BC557B/BC558B		180	460	
	BC557C/BC558C		420	800	
Collector-emitter saturation voltage (Ic=-100mA, IB=-5mA)		VCE(sat)	-	-0.3	V
Base-emitter saturation voltage (Ic=-100mA, IB=-5mA)		VBE(sat)	-	-1	V
<b>Transition frequency</b> (VCE=-5V, IC=-10mA, f=100MHz)		f <sub>T</sub>	150	-	MHz



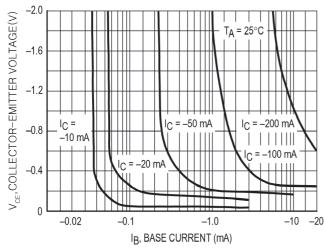
#### BC557/BC558

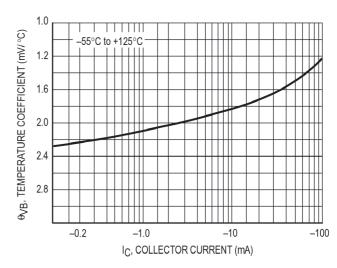




**Normalized DC Current Gain** 

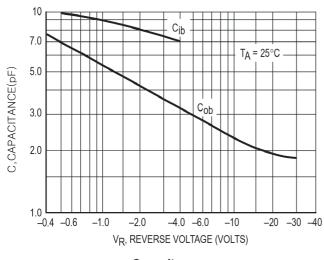
"Saturation" and "On" Voltages

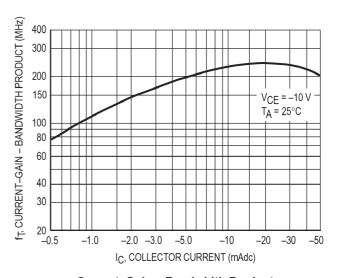




Collector Saturation Region

**Base-Emitter Temperature Coefficient** 

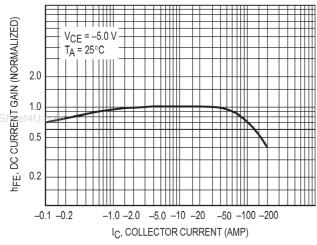




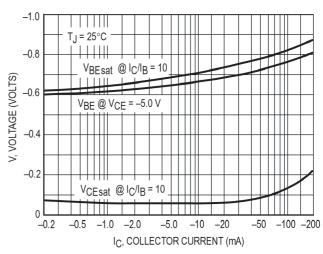
Capacitances Current-Gain - Bandwidth Product



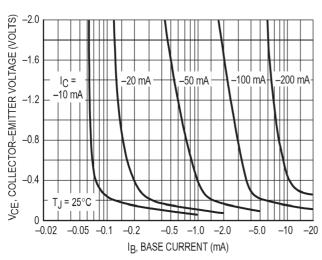




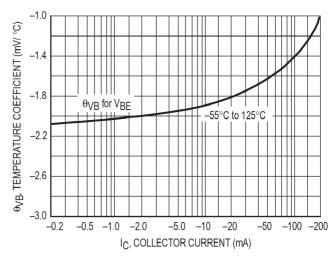
**DC Current Gain** 



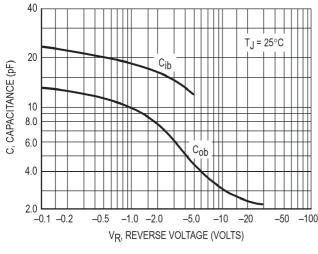
"On" Voltage



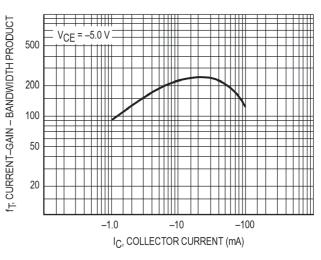
**Collector Saturation Region** 



**Base-Emitter Temperature Coefficient** 



Capacitance

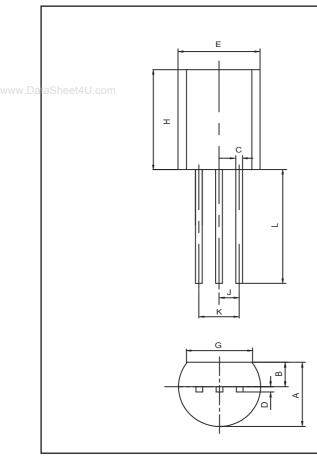


Current-Gain - Bandwidth Product



# **TO-92 Outline Dimensions**

unit:mm



<b>TO-92</b>				
Dim	Min	Max		
A	3.30	3.70		
В	1.10	1.40		
C	0.38	0.55		
D	0.36	0.51		
E	4.40	4.70		
G	3.43	-		
H	4.30	4.70		
J	1.270TYP			
K	2.44	2.64		
L	14.10	14.50		